

N-channel TrenchMOS logic level FET 18 August 2015

Product data sheet

1. General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

2. Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance

3. Applications

• Automotive and general purpose power switching

4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	100	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	23	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	98	W
Static chara	cteristics		1				
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; Fig. 12		-	55	72	mΩ
		V_{GS} = 5 V; I _D = 10 A; T _j = 25 °C; <u>Fig. 12</u>		-	60	75	mΩ
Avalanche r	uggedness						
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 23 A; $V_{sup} \le 100$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[1][2]	-	-	100	mJ

[1] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[2] Refer to application note AN10273 for further information.

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G-UF4
mb	D	mounting base; connected to drain	D2PAK (SOT404)	mbb076 S

6. Ordering information

Table 3. Ordering information								
Type number	Package							
	Name	Description	Version					
BUK9675-100A	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404					

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK9675-100A	BUK9675-100A

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	100	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ	-	100	V
V _{GS}	gate-source voltage		-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	98	W
I _D	drain current	T _{mb} = 100 °C; V _{GS} = 5 V; <u>Fig. 2</u>	-	16	А
		T _{mb} = 25 °C; V _{GS} = 5 V; <u>Fig. 2</u>	-	23	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 3	-	92	А
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
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Symbol	Parameter	Conditions		Min	Мах	Unit
Source-dra	in diode					
I _S	source current	T _{mb} = 25 °C		-	23	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	92	А
Avalanche	ruggedness		1			
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 23 A; V _{sup} ≤ 100 V; R _{GS} = 50 Ω; V _{GS} = 5 V; T _{j(init)} = 25 °C; unclamped; Fig. 4	[1][2]	-	100	mJ

Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
Refer to application note AN10273 for further information.

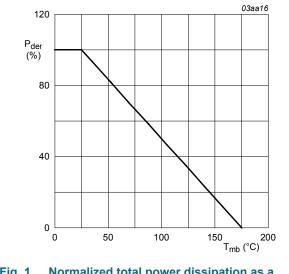


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

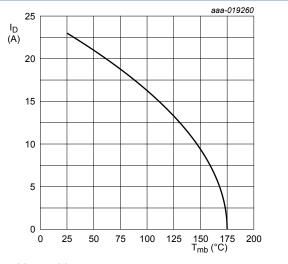
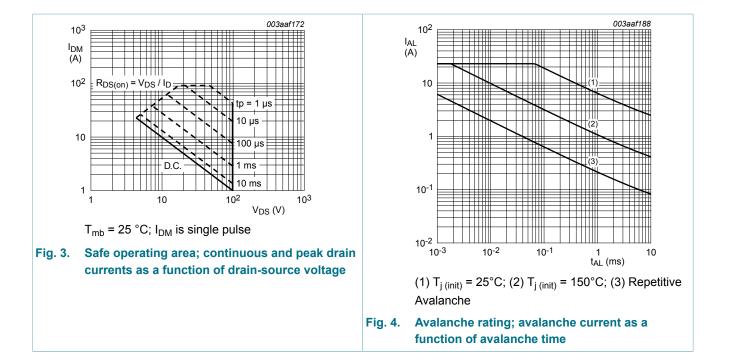




Fig. 2. Continuous drain current as a function of mounting base temperature

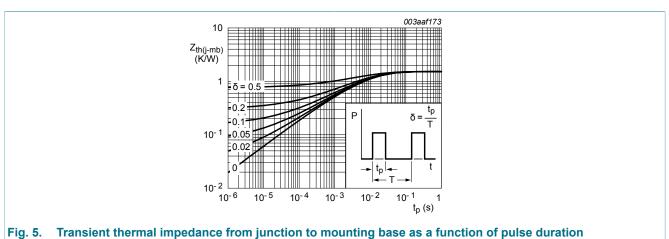
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9. Thermal characteristics

Thermal characteristics Table 6. Conditions **Symbol** Parameter Unit Min Тур Max thermal resistance 1.5 K/W R_{th(j-mb)} _ from junction to mounting base R_{th(j-a)} thermal resistance Minimum footprint; FR4 board 50 K/W from junction to ambient



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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · · · · · · · · · · · · · · · · ·				
V _{(BR)DSS}	drain-source	I_D = 0.25 mA; V_{GS} = 0 V; T_j = 25 °C	100	-	-	V
	breakdown voltage	I _D = 0.25 mA; V _{GS} = 0 V; T _j = -55 °C	89	-	-	V
V _{GS(th)} gate-source the voltage	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 10; Fig. 11	1	1.5	2	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	2.3	V
I _{DSS}	drain leakage current	V _{DS} = 100 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C	-	0.05	10	μA
I _{GSS}	gate leakage current	V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; Fig. 12	-	55	72	mΩ
		V _{GS} = 5 V; I _D = 10 A; T _j = 175 °C; Fig. 13	-	-	188	mΩ
		V _{GS} = 4.5 V; I _D = 10 A; T _j = 25 °C; Fig. 12	-	61	84	mΩ
		V_{GS} = 5 V; I _D = 10 A; T _j = 25 °C; <u>Fig. 12</u>	-	60	75	mΩ
Dynamic ch	naracteristics	· · · · · ·				
Q _{G(tot)}	total gate charge	I _D = 10 A; V _{DS} = 80 V; V _{GS} = 5 V;	-	24.3	-	nC
Q _{GS}	gate-source charge	Fig. 14; Fig. 15	-	3	-	nC
Q _{GD}	gate-drain charge		-	12.2	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;	-	1278	1704	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 16</u>	-	129	155	pF
C _{rss}	reverse transfer capacitance		-	88	120	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R _L = 1.2 Ω; V _{GS} = 5 V;	-	13	20	ns
t _r	rise time	R _{G(ext)} = 10 Ω; T _j = 25 °C	-	120	168	ns
t _{d(off)}	turn-off delay time		-	58	87	ns
t _f	fall time		-	57	86	ns
L _D	internal drain inductance	from drain lead 6 mm from package to centre of die; $T_i = 25 \text{ °C}$	-	4.5	-	nH

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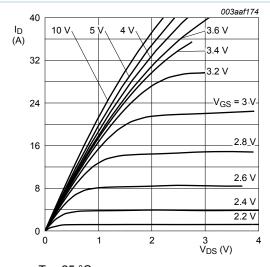
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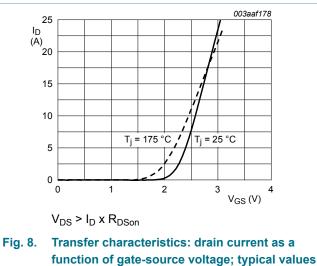
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		from upper edge of drain tab to centre of die; $T_j = 25 \text{ °C}$	-	2.5	-	nH
L _S	internal source inductance	from source lead to source bond pad; $T_j = 25 \ ^{\circ}C$	-	7.5	-	nH
Source-drain	n diode					
V _{SD}	source-drain voltage	I_{S} = 10 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 17</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_{\rm S}$ = 20 A; dI_{\rm S}/dt = -100 A/µs; V_{\rm GS} = 0 V;	-	53.7	-	ns
Qr	recovered charge	V _{DS} = 30 V; T _j = 25 °C	-	126	-	nC

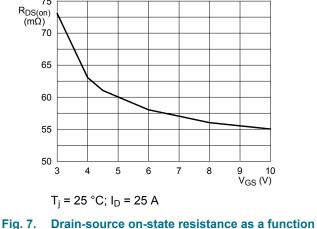
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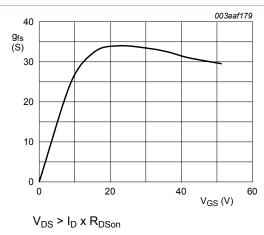
T_i = 25 °C







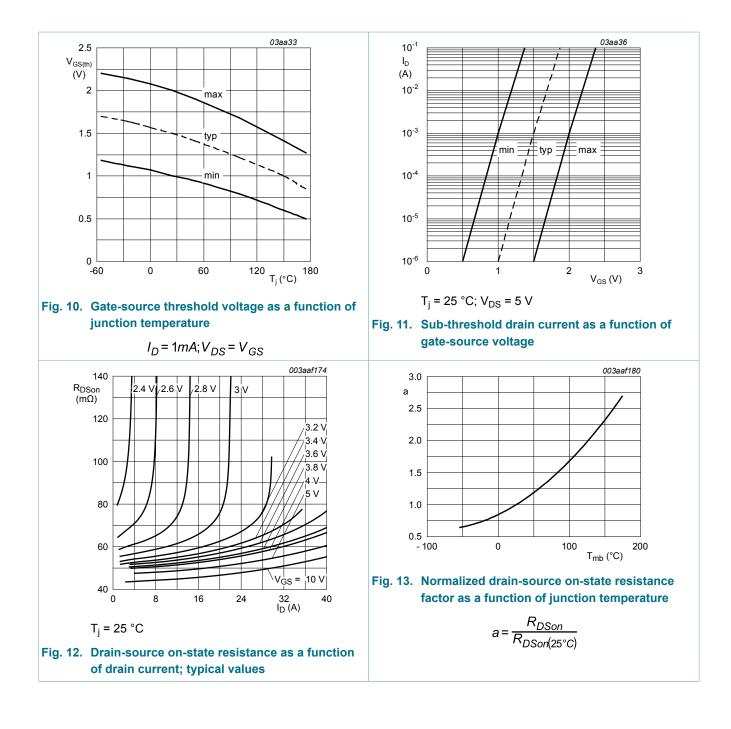




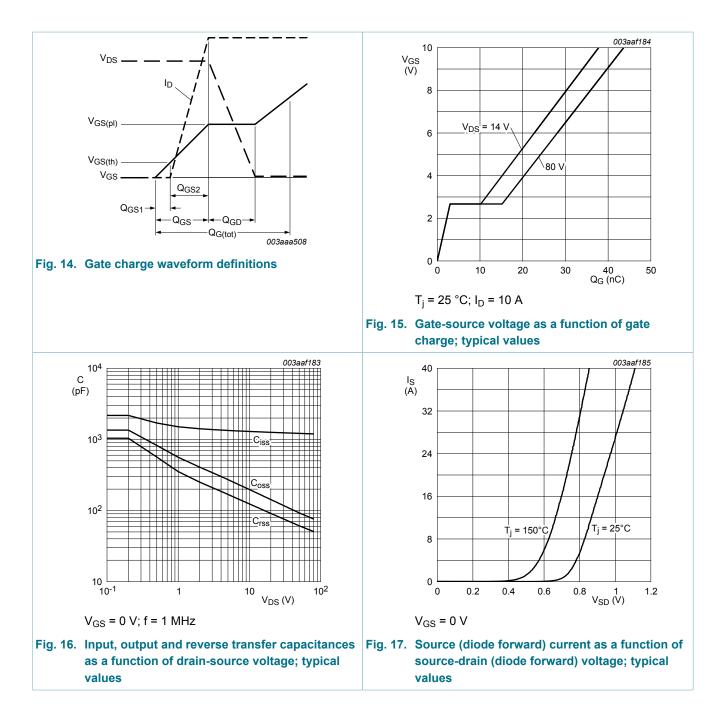


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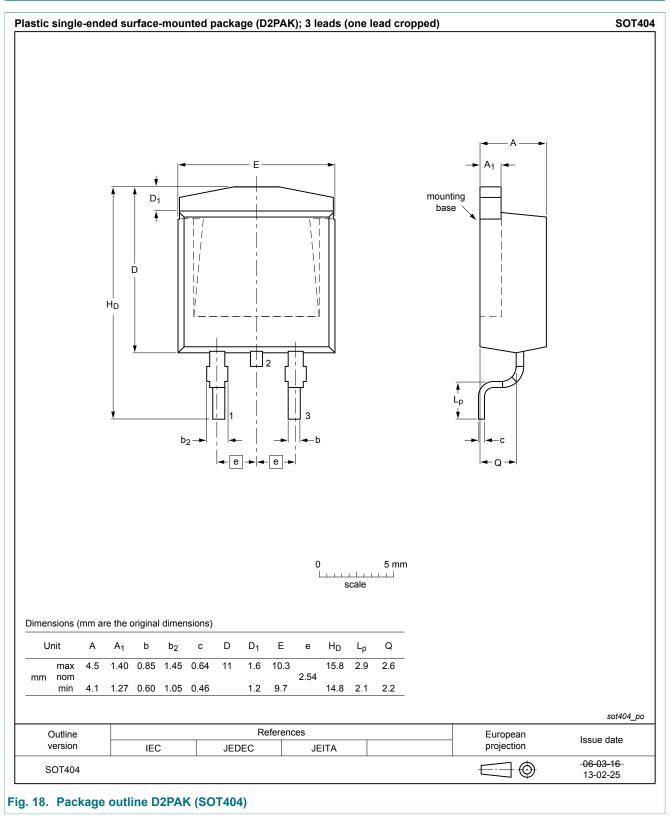


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11. Package outline



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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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